

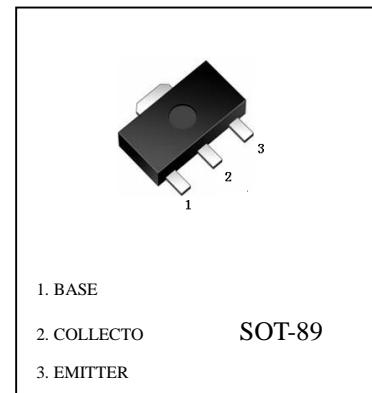
FEATURES

Excellent current-to-gain characteristics
 Low collector saturation voltage V_{CE(sat)}
 V_{CE(sat)}=0.5V(max) for IC/IB=2A/0.1A

2SD2150(NPN)

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current -Continuous	I _C	2000	mA
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{Stg}	-55-150	°C



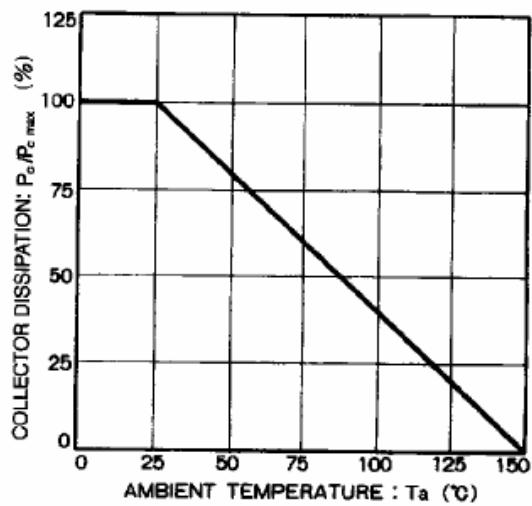
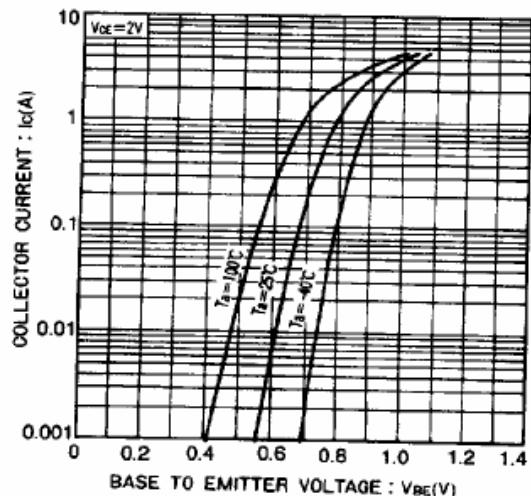
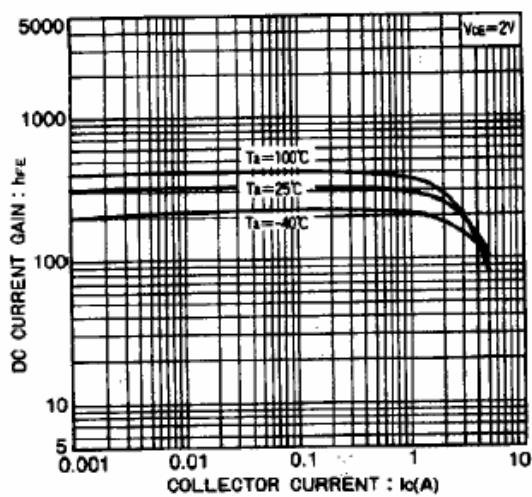
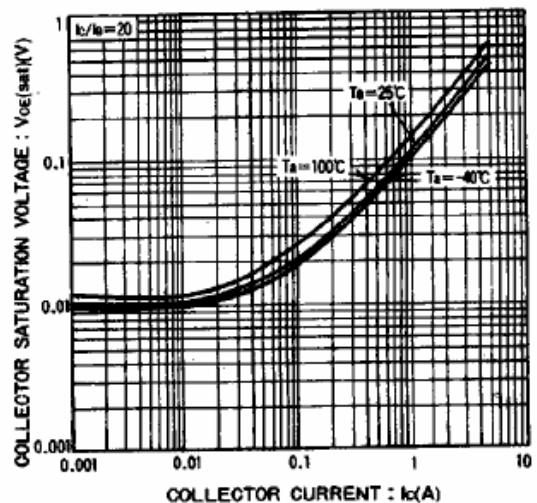
ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =50uA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =1mA, I _B =0	20			V
Emitter-base breakdown voltage	V _{EBO}	I _E =50μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE} *	V _{CE} =2V, I _C =100mA	180		560	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =2A, I _B =100mA			0.5	V
Transition frequency	f _{T*}	V _{CE} =2V, I _C =500mA f=100MHz		290		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		25		pF

*Pulse test: t_p≤300μS, δ≤0.02.

CLASSIFICATION OF HFE

Marking	CFR	CFS		
Range	180-390	270-560		

2SD2150 Typical Characteristics

Figure 1

Figure 2

Figure 3

Figure 4